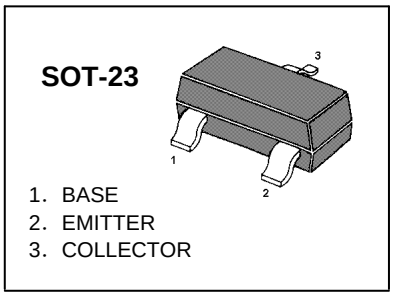
TRANSISTOR（NPN）

FEATURES

Complementary to S9012

Excellent h_{FE} linearity

MARKING: J3



MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Power Dissipation	300	mW
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=0.1mA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	uA
Collector cut-off current	I_{CEO}	V_{CE}=20V, I_B=0			0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			0.1	uA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C=50mA	120		400	
	$h_{FE(2)}$	V_{CE}=1V, I_C=500mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=500mA, I_B=50mA			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=500mA, I_B=50mA			1.2	V
Base-emitter voltage	V_{BE}	V_{CB}=1V,I_C=10mA,			0.7	V
Transition frequency	f_T	V_{CE}=6V,I_C=20mA, f=30MHz	150			MHz
Collector output capacitance	C_{ob}	V_{CB}=6V, I_E=0, f=1MHz			8	pF

CLASSIFICATION OF $h_{FE(1)}$

RANK	L	H	J
RANGE	120-200	200-350	300-400

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Typical Characteristics S9013

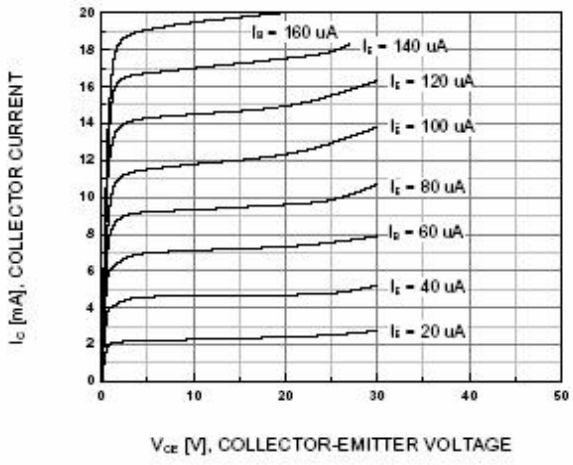


Figure 1. Static Characteristic

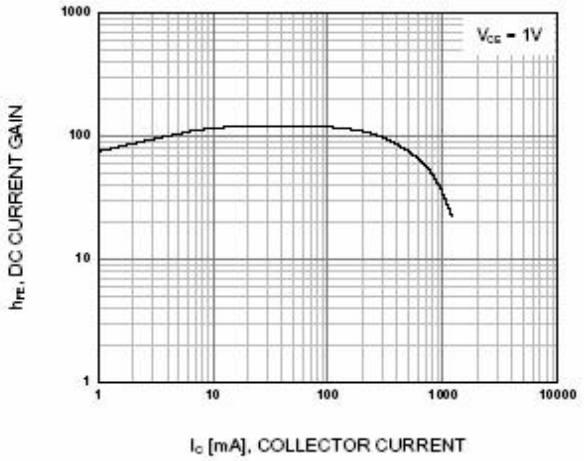


Figure 2. DC current Gain

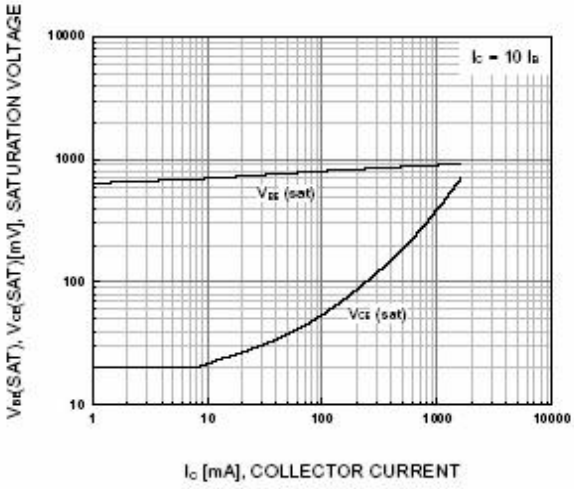


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

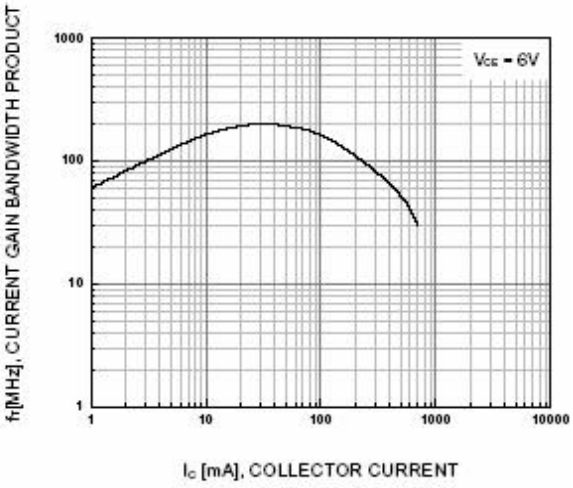


Figure 4. Current Gain Bandwidth Product

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